

/

IDM

7	28	2020	2020	
30.63		16.03%	4.03	145.27%
	3.45		466.46%	

IDM			2020	
30.63		16.03%	IDM	13.69
	20.11%		16.77	
12.78%		27.3%	6.63	

IDM
 IGBT 49.90% MOSFET 21.43%
 50% IDM
 11.5%
 27.3% 6.63
 2019.

2019

IDM 44.71% 42.18%

1

单位: 万元	2019H1	2019	2019H2	2019H3	同比 (2019H3 2019H1)	环比 (2019H3 2019H2)
制造与研发	148672.05	148672.05	148672.05	148672.05	148672.05	148672.05
晶圆制造	105984.39	105984.39	105984.39	105984.39	105984.39	105984.39
封装测试	36930.19	36930.19	36930.19	36930.19	36930.19	36930.19
产品与方案	114006.51	114006.51	114006.51	114006.51	114006.51	114006.51
功率半导体	102793.73	102793.73	102793.73	102793.73	102793.73	102793.73
其他	3019.73	3019.73	3019.73	3019.73	3019.73	3019.73
其他业务	1323.84	1323.84	1323.84	1323.84	1323.84	1323.84
合计	204508.59	204508.59	204508.59	204508.59	204508.59	204508.59

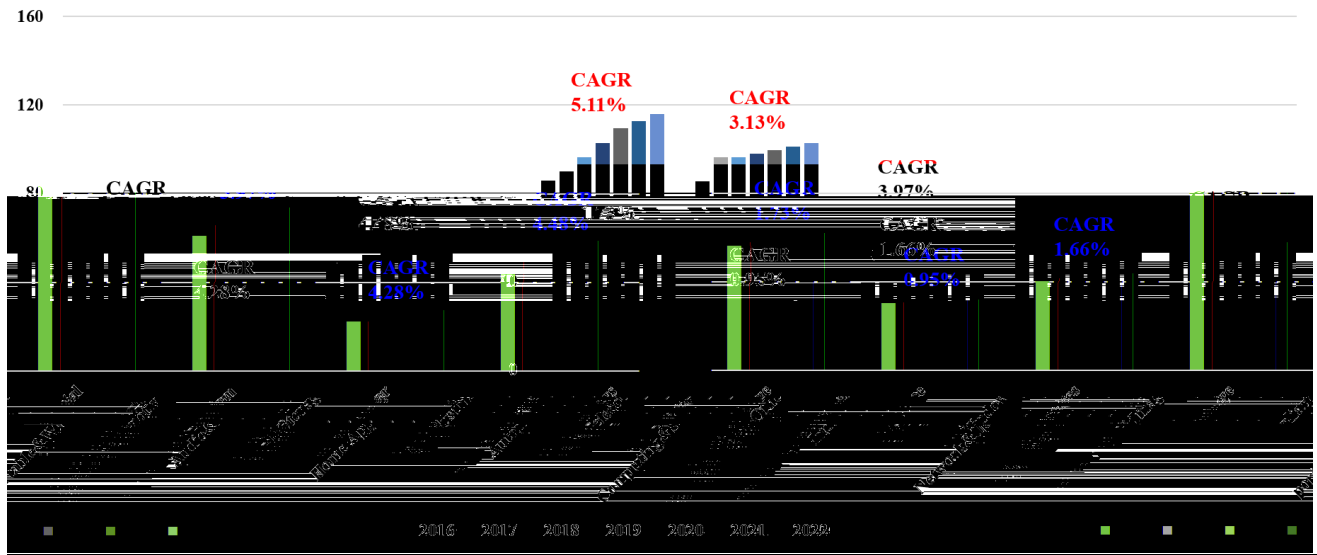
Wind

1200V 650V SiC

6 SiC

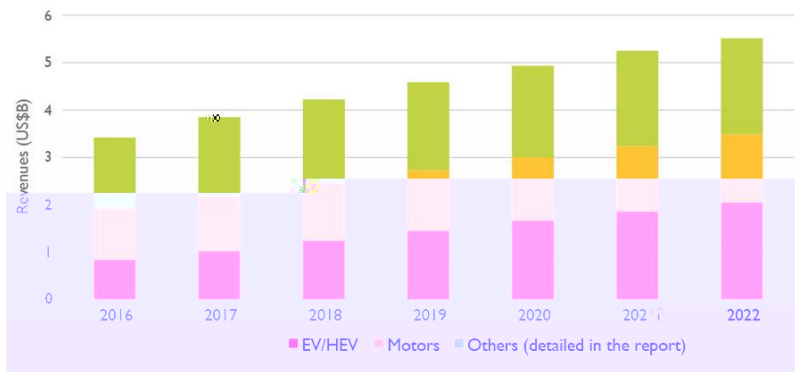
2 MOSFET

2016-2022功率MoSFET细分应用市场规模预测（亿元）



Yole

3 IGBT



Yole

2018

1

2016

4

2016 2017

“ ”

AA

ABS

R3

A

B

“ ”

		6	15%
		6	5% 15%
		6	-5% 5%
		6	5% 15%
		6	15%
		6	
		6	
		6	

<http://www.nesc.cn>

400-600-0686

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28	D		100033
729			200127
1006	34D		518038
	122	15	510630

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